



PRESS - PACK RECTIFIER DIODE

D123-320

| | | |
|---|--|--|
| ◆ $V_{RRM} = \underline{3400-4200 \text{ V}}$ | | |
| ◆ Low forward losses ◆ Low dispersion Q_{RR} and V_{FM} for series and parallel connections ◆ Press-pack design | | |

MAXIMUM RATED VALUES

| Parameter and conditions | Symbol | Values | Units |
|---|-------------|-----------------|----------------------|
| Repetitive peak reverse voltage, $T_j = -60 \dots + 150 \text{ }^\circ\text{C}$ | V_{RRM} | 3400-4200 | V |
| Non-repetitive peak reverse voltage, $T_j = -60 \dots + 150 \text{ }^\circ\text{C}$ | V_{RSM} | 3500-4300 | |
| Repetitive peak reverse current, $T_j = 150 \text{ }^\circ\text{C}, V_R = V_{RRM}$ | I_{RRM} | 35 | mA |
| Maximum average forward current, $T_C = 85 \text{ }^\circ\text{C}, f = 50 \text{ Hz}$ | $I_{F(AV)}$ | 410 | A |
| RMS forward current, $T_C = 85 \text{ }^\circ\text{C}, f = 50 \text{ Hz}$ | I_{FRMS} | 644 | |
| Surge non-repetitive current, $T_j = 150 \text{ }^\circ\text{C}, V_R = 0, t_p = 10 \text{ ms}$ | I_{FSM} | 4,2 | kA |
| Safety factor | I^2t | $88 \cdot 10^3$ | A^2s |
| Operation junction temperature range | T_j | -60 ... +150 | ${}^\circ\text{C}$ |
| Storage temperature range | T_{stg} | -60 ... +50 | |



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| ELECTRICAL CHARACTERISTICS | | | | | |
|--|---------------|--------|-------|----------------------|-----------------------|
| Parameter and conditions | Symbol | Values | | | Units |
| | | min | typ. | max | |
| Maximum peak forward voltage, $T_j = 25^\circ\text{C}$, $I_F = 1000 \text{ A}$ | V_{FM} | - | - | 2,05 | V |
| On-state threshold voltage, $T_j = 150^\circ\text{C}$, $I_F = 500 - 1500 \text{ A}$ | V_{TO} | - | - | 0,87 | |
| On-state slope resistance, $T_j = 150^\circ\text{C}$, $I_F = 500 - 1500 \text{ A}$ | r_T | - | - | 1,370 | $\text{m}\Omega$ |
| Recovery charge, $T_j = 150^\circ\text{C}$, $I_F = 320 \text{ A}$, $di_F/dt = -5 \text{ A}/\mu\text{s}$, $V_R \geq 100 \text{ V}$ | Q_{RR} | - | - | | μAs |
| Recovery current, $T_j = 150^\circ\text{C}$, $I_F = 320 \text{ A}$, $di_F/dt = -5 \text{ A}/\mu\text{s}$, $V_R \geq 100 \text{ V}$ | I_{RR} | - | - | | A |
| THERMAL PARAMETERS | | | | | |
| Thermal resistance junction to case, DC per diode double side cooled anode side cooled cathode side cooled | $R_{th(j-c)}$ | - | - | 0,08 0,16 0,16 | °C/W |
| Thermal resistance case to heatsink, double side cooled single side cooled | R_{thch} | - | - | 0,02 0,04 | |
| MECHANICAL PARAMETERS | | | | | |
| Weight | w | - | 0,091 | - | kg |
| Mounting force | F | 5 | | 7 | kN |
| Maximum acceleration (at nominal mounting force) | a | - | - | 100 | m/s^2 |



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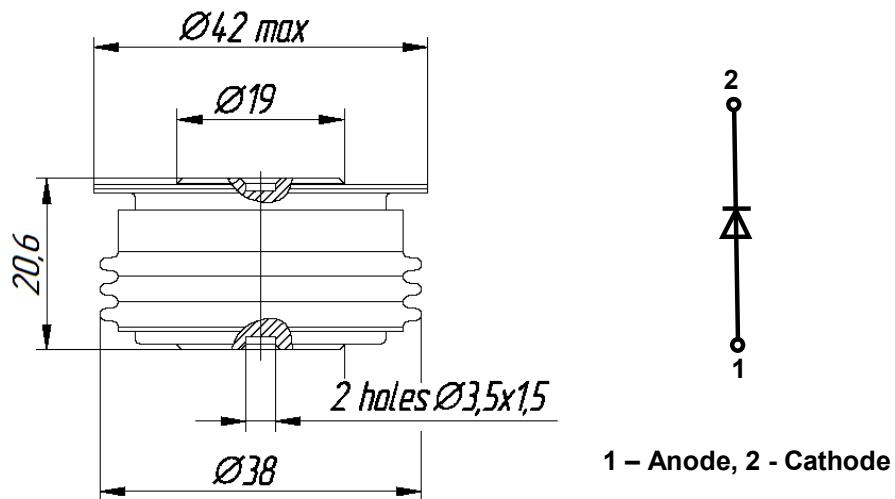


Fig. 1. Device Outline Drawing
(dimensions in mm)



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